

Silicon PNP Power Transistors

2SA626

DESCRIPTION

- With TO-3 package
- Wide area of safe operation
- High current capability: $I_C=-6A$

APPLICATIONS

- For audio frequency output applications

PINNING(see Fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

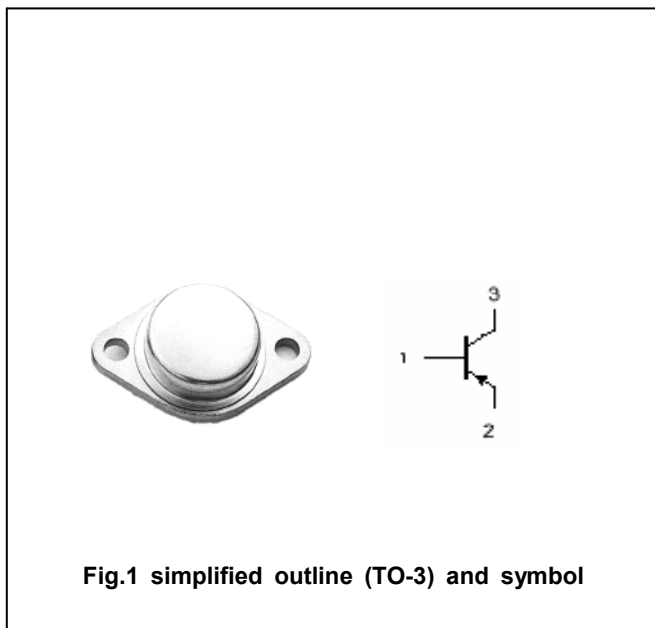


Fig.1 simplified outline (TO-3) and symbol

Absolute maximum ratings($T_a=\square$)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	-80	V
V_{CEO}	Collector-emitter voltage	Open base	-80	V
V_{EBO}	Emitter-base voltage	Open collector	-6	V
I_C	Collector current		-6	A
I_{CM}	Collector current-peak		-10	A
P_C	Collector power dissipation	$T_C=25\square$	60	W
T_j	Junction temperature		150	\square
T_{stg}	Storage temperature		-55~150	\square

Silicon PNP Power Transistors

2SA626

CHARACTERISTICS

T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =-25mA ; I _B =0	-80			V
V _{(BR)CBO}	Collector-base breakdown voltage	I _C =-1mA ; I _E =0	-80			V
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E =-1mA ; I _C =0	-6			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =-4A ; I _B =-0.4A			-2.0	V
V _{BEsat}	Base-emitter saturation voltage	I _C =-4A ; I _B =-0.4A			-2.5	V
I _{CBO}	Collector cut-off current	V _{CB} =-80V ; I _E =0			-0.1	mA
I _{EBO}	Emitter cut-off current	V _{EB} =-6V ; I _C =0			-0.1	mA
h _{FE}	DC current gain	I _C =-2A ; V _{CE} =-5V	30		120	
f _T	Transition frequency	I _C =-1A ; V _{CE} =-5V		15		MHz

Silicon PNP Power Transistors

2SA626

PACKAGE OUTLINE



Fig.2 outline dimensions (unindicated tolerance:±0.1mm)